

# FDP8N50NZ / FDPF8N50NZ N-Channel UniFET™ II MOSFET 500 V, 8 A, 850 mΩ

## Features

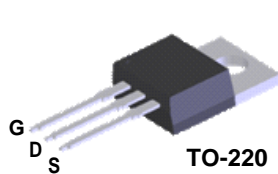
- $R_{DS(on)} = 770\text{ m}\Omega$  (Typ.) @  $V_{GS} = 10\text{ V}$ ,  $I_D = 4\text{ A}$
- Low Gate Charge (Typ. 14 nC)
- Low  $C_{rss}$  (Typ. 5 pF)
- 100% Avalanche Tested
- Improve dv/dt Capability
- ESD Improved Capability
- RoHS Compliant

## Applications

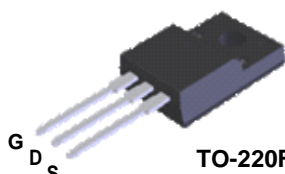
- LCD/LED TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

## Description

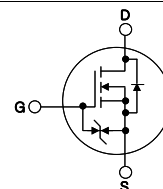
UniFET™ II MOSFET is Fairchild Semiconductor®'s high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220



TO-220F



## MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FDP8N50NZ	FDPF8N50NZ	Unit
$V_{DSS}$	Drain to Source Voltage	500		V
$V_{GSS}$	Gate to Source Voltage	$\pm 25$		V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	8	A
		- Continuous ( $T_C = 100^\circ\text{C}$ )	4.8	
$I_{DM}$	Drain Current	- Pulsed (Note 1)	32	A
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	122	mJ
$I_{AR}$	Avalanche Current	(Note 1)	8	A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	13	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	10	V/ns
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	130	W
		- Derate above $25^\circ\text{C}$	1	
$T_J, T_{STG}$	Operating and Storage Temperature Range	$-55$ to $+150$		$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$

\*Drain current limited by maximum junction temperature

## Thermal Characteristics

Symbol	Parameter	FDP8N50NZ	FDPF8N50NZ	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.96	3.1	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case to Sink, Typ.	0.5	-	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP8N50NZ	FDP8N50NZ	TO-220	-	-	50
FDPF8N50NZ	FDPF8N50NZ	TO-220F	-	-	50

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$ , $T_C = 25^\circ\text{C}$	500	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.5	-	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{V}$ , $V_{GS} = 0\text{V}$ $V_{DS} = 400\text{V}$ , $T_C = 125^\circ\text{C}$	-	-	1 10	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 25\text{V}$ , $V_{DS} = 0\text{V}$	-	-	$\pm 10$	$\mu\text{A}$

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$ , $I_D = 4\text{A}$	-	0.77	0.85	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20\text{V}$ , $I_D = 4\text{A}$	-	6.3	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	565	735	pF
$C_{oss}$	Output Capacitance		-	80	105	pF
$C_{rss}$	Reverse Transfer Capacitance		-	5	8	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 400\text{V}$ , $I_D = 8\text{A}$ $V_{GS} = 10\text{V}$ (Note 4)	-	14	18	nC
$Q_{gs}$	Gate to Source Gate Charge		-	4	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	6	-	nC

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{V}$ , $I_D = 8\text{A}$ $R_G = 25\Omega$ , $V_{GS} = 10\text{V}$ (Note 4)	-	17	45	ns
$t_r$	Turn-On Rise Time		-	34	80	ns
$t_{d(off)}$	Turn-Off Delay Time		-	43	95	ns
$t_f$	Turn-Off Fall Time		-	27	60	ns

### Drain-Source Diode Characteristics

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current	-	-	8	A	
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current	-	-	30	A	
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>SD</sub> = 8A	-	-	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>SD</sub> = 8A	-	228	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt = 100A/μs	-	1.43	-	μC

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L = 3.8\text{mH}$ ,  $I_{AS} = 8\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 8\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Essentially Independent of Operating Temperature Typical Characteristics

# Typical Performance Characteristics

Figure 1. On-Region Characteristics

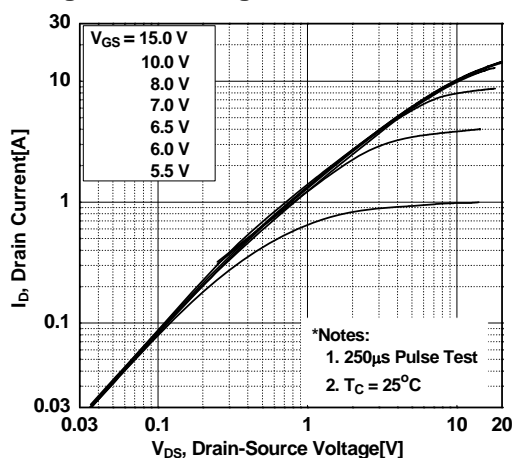


Figure 2. Transfer Characteristics

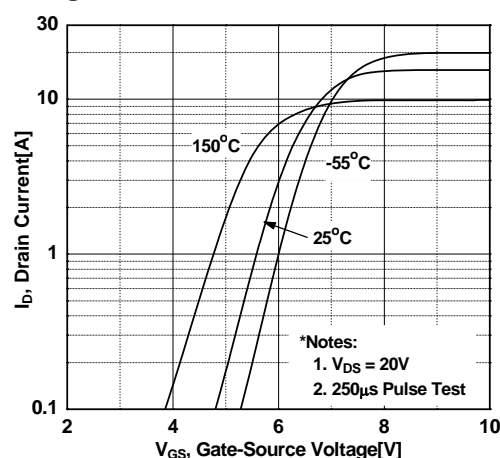


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

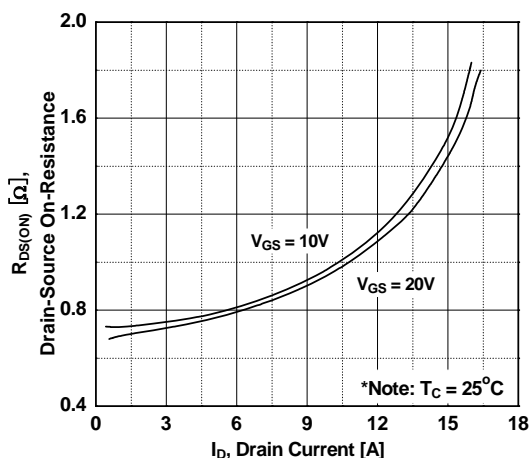


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

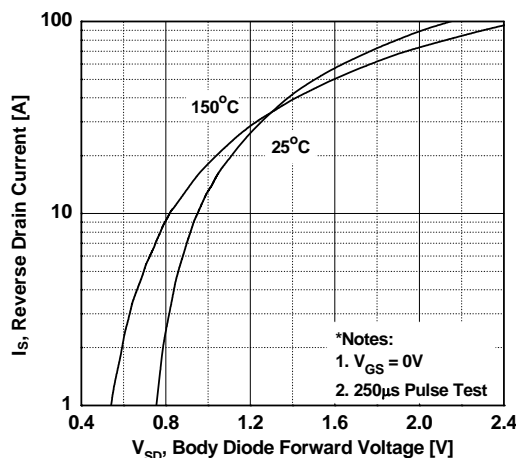


Figure 5. Capacitance Characteristics

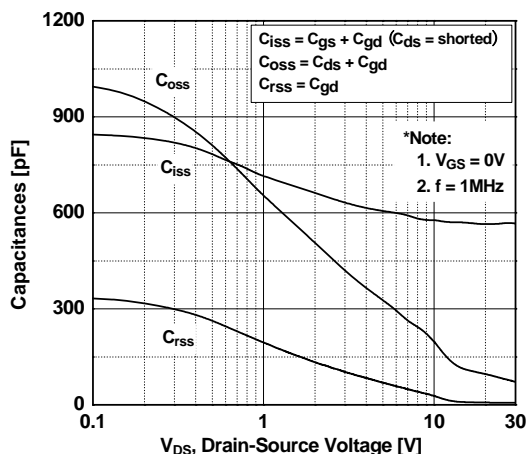
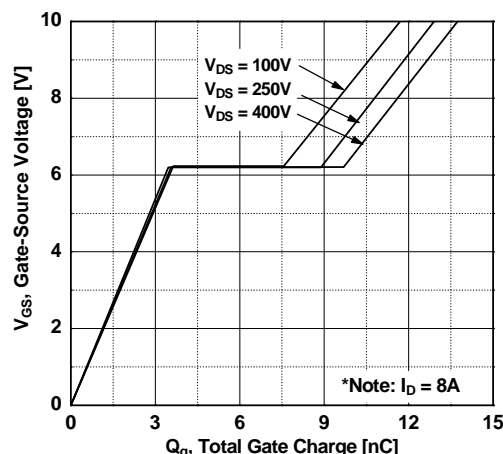
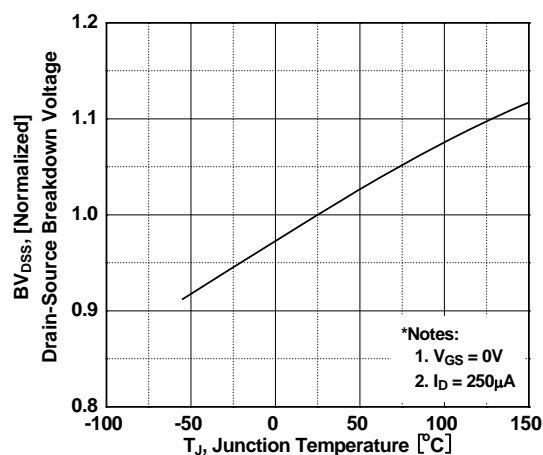


Figure 6. Gate Charge Characteristics

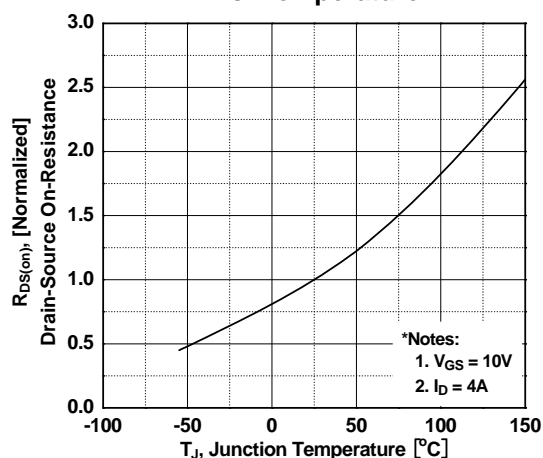


## Typical Performance Characteristics (Continued)

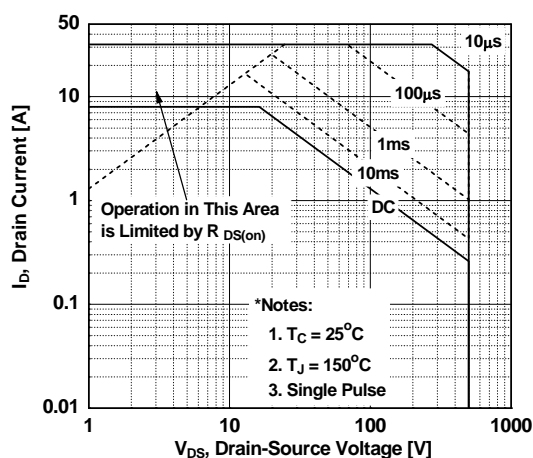
**Figure 7. Breakdown Voltage Variation vs. Temperature**



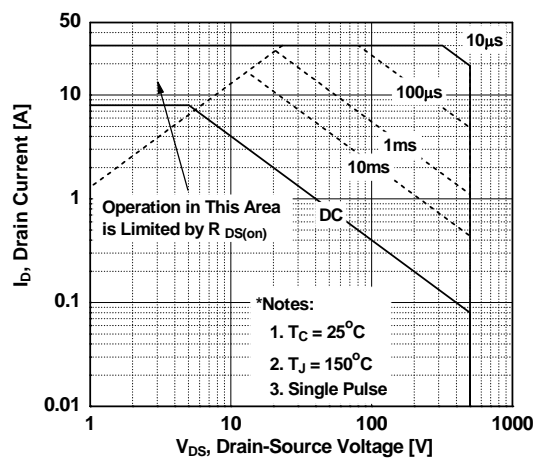
**Figure 8. On-Resistance Variation vs. Temperature**



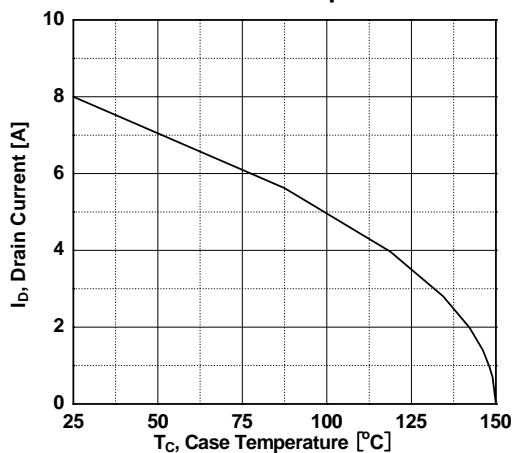
**Figure 9. Maximum Safe Operating Area - FDP8N50NZ**



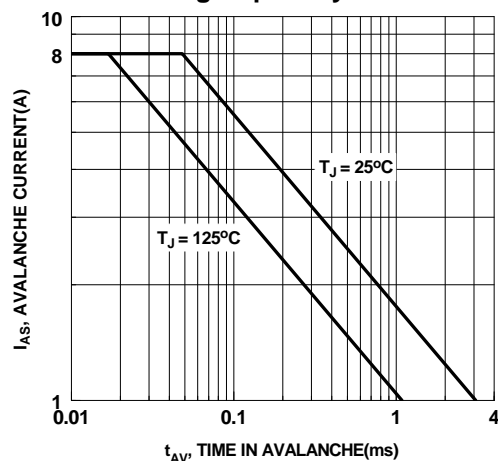
**Figure 10. Maximum Safe Operating Area - FDPF8N50NZ**



**Figure 11. Maximum Drain Current vs. Case Temperature**



**Figure 12. Unclamped Inductive Switching Capability**



# Typical Performance Characteristics (Continued)

Figure 13. Transient Thermal Response Curve - FDP8N50NZ

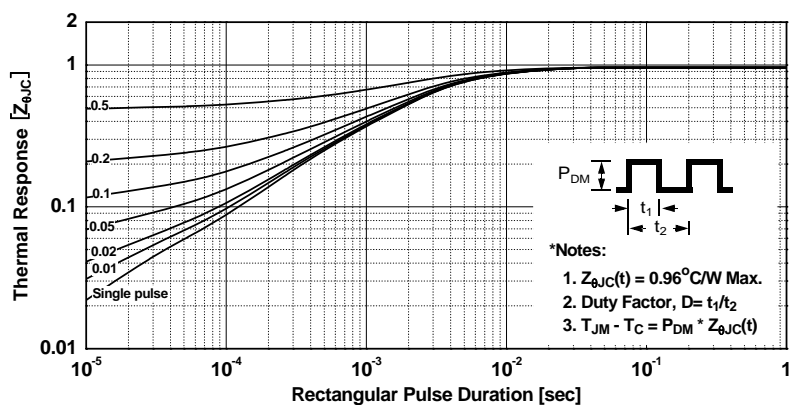
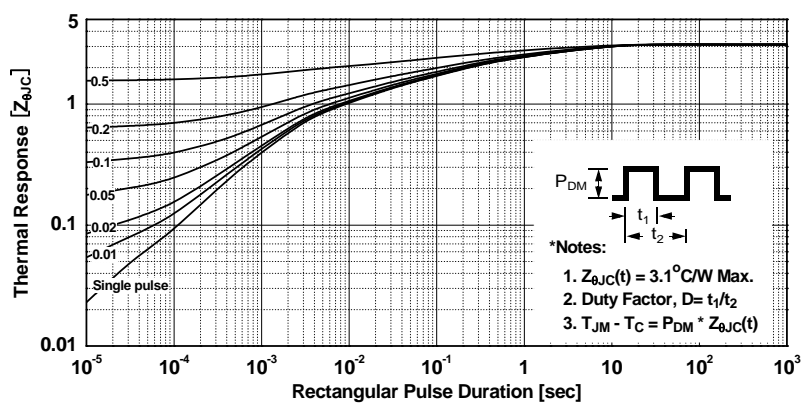
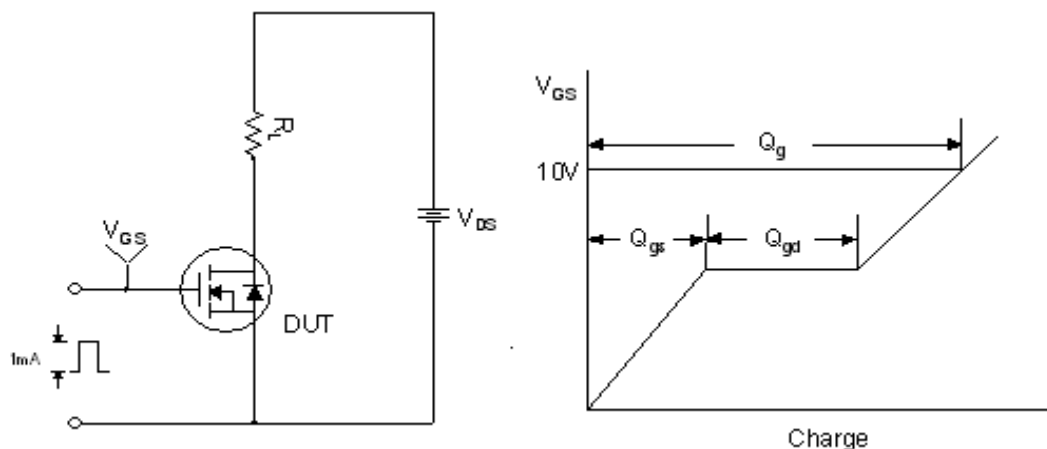


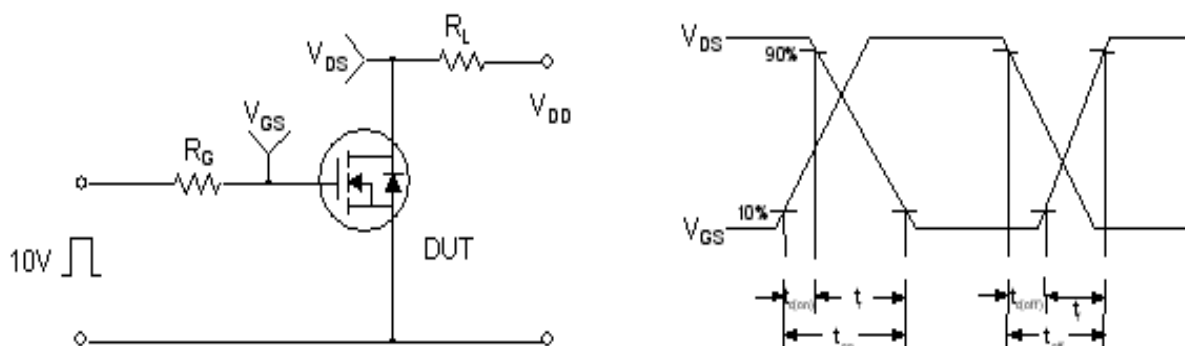
Figure 14. Transient Thermal Response Curve - FDPF8N50NZ



Gate Charge Test Circuit & Waveform



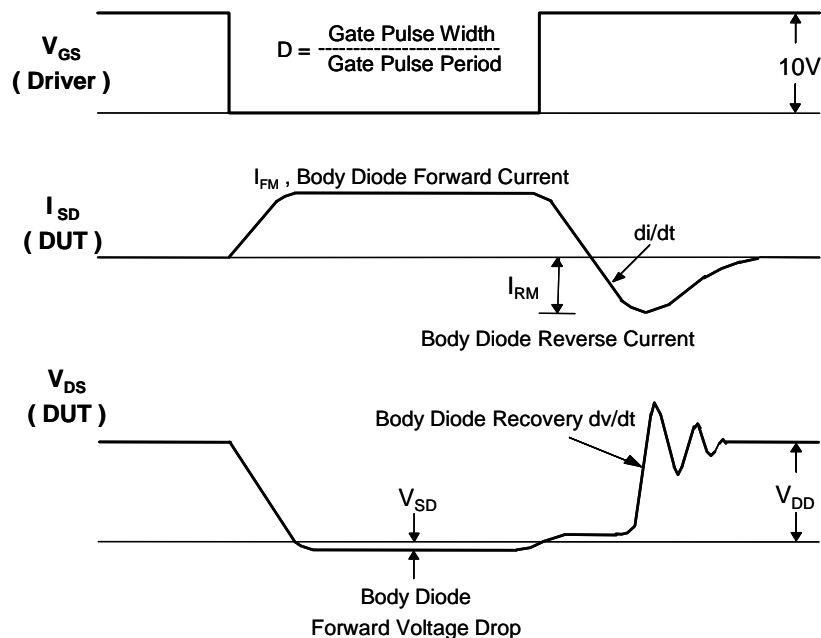
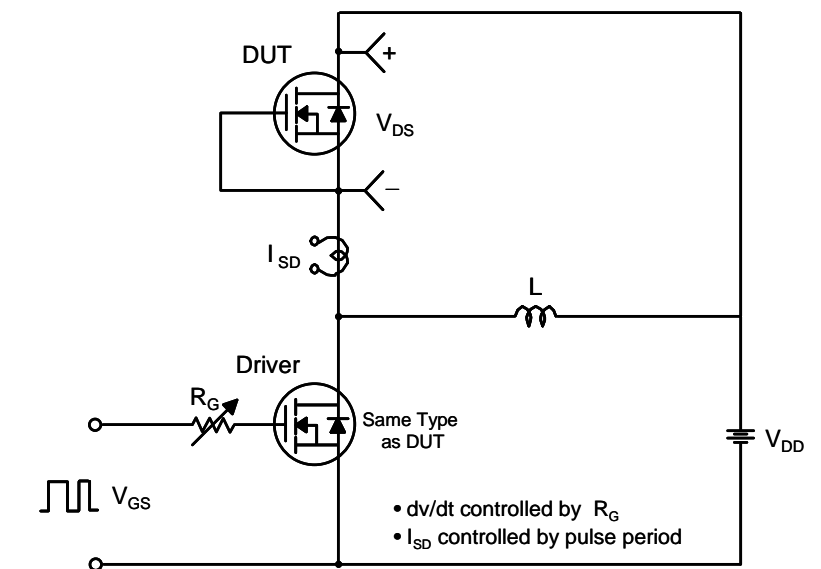
Resistive Switching Test Circuit & Waveforms



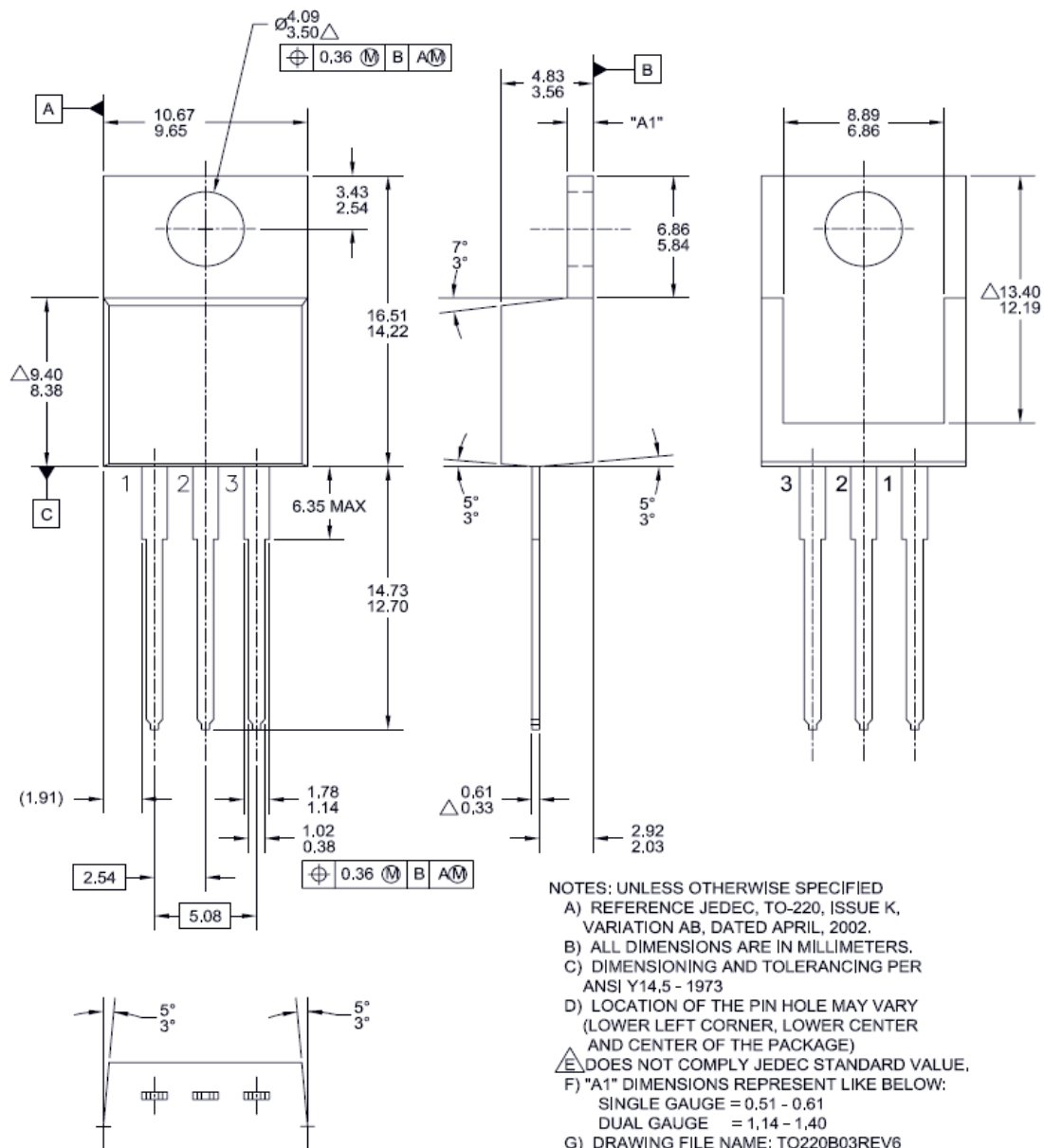
Unclamped Inductive Switching Test Circuit & Waveforms



# Peak Diode Recovery dv/dt Test Circuit & Waveforms



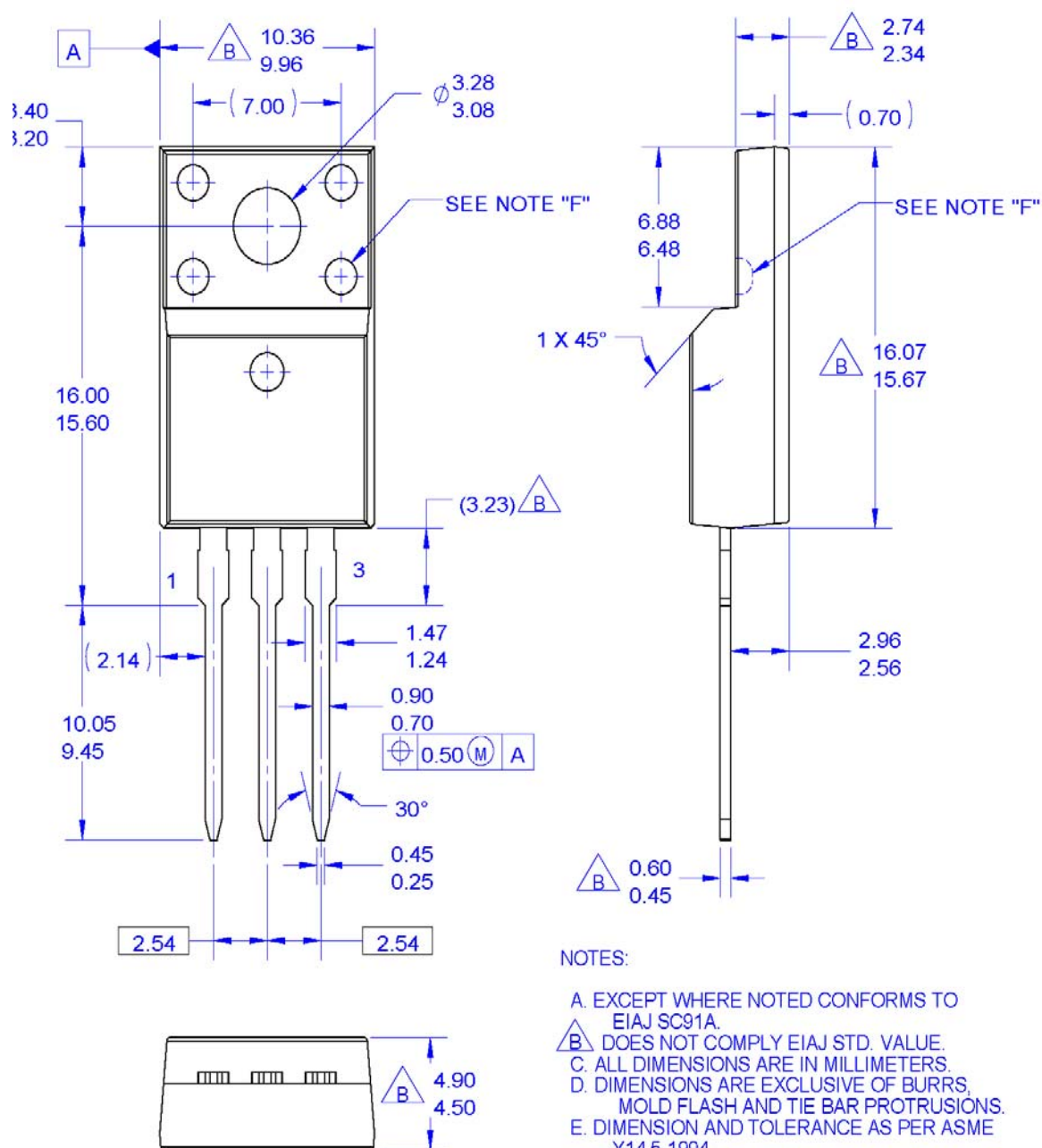
TO-220B03





# Package Dimensions

## TO-220M03



### NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.  
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV3

Dimensions in Millimeters



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CTL™	GTO™	Saving our world, 1mW/W/kW at a time™	TinyPWM™
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Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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